#### **PATENT**

# THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Bo Su Chen, et al.

Serial No.:

10/622,042

Examiner: unknown

Filing Date:

July 17, 2003

Group Art: unknown

For: OPTICAL COUPLING SYSTEM

Docket No.: H0004315 (1139.1131101)

#### TRANSMITTAL SHEET

**Assistant Commissioner for Patents** PO Box 1450 Alexandria, VA 22313-1450

CERTIFICATE UNDER 37 C.F.R. 1.8: I hereby certify that this correspondence is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to the: Commissioner for Patents, PO Box 1450, Alexandria, VA 22313-1450, on this 13th day of November, 2003.

John G. Shudy, Jr.

We are transmitting herewith the attached:

Information Disclosure Statement, Form PTO-1449 and 89 cited non-US patent [X]

references.

Please charge any deficiencies or credit any overpayment in the enclosed fees to [X]

Deposit Account No. 50-0413.

John G. Shudy, Jr., Reg. No. 31,214

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#### **INFORMATION DISCLOSURE STATEMENT (37 C.F.R. §1.97(b))**

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John G. Shudy, Jr.

Dear Sir:

With regard to the above-identified application, the items of information listed on the enclosed Form 1449 are brought to the attention of the Examiner.

This statement should be considered because it is submitted before the mailing date of a first Office Action on-the-merits. Accordingly, no fee is due for consideration of the items listed on the enclosed Form 1449.

In accordance with 37 C.F. R. §1.98(a)(2), a copy of each non-US patent or other information listed on the enclosed Form 1449 is provided.

No representation is intended to be made hereby that any of the cited references establishes, by itself or in combination with other information, a prima facie case of unpatentability of any claim of the present case.

Consideration of the items listed is respectfully requested. Pursuant to the provisions of M.P.E.P. 609, it is requested the Examiner return a copy of the attached Form 1449, marked as being considered and initialed by the Examiner, to the undersigned with the next official communication.

Respectfully submitted,

Bo Su Chen, et al.

By their attorney,

John G. Shudy, Jr., Reg. No. 31,214

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# LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

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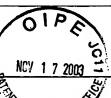
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